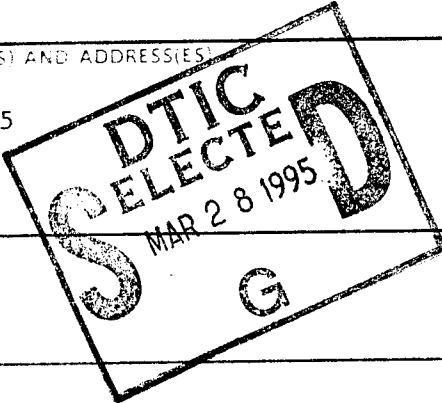


# REPORT DOCUMENTATION PAGE

Form Approved  
OMB No. 0704-0188

Public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington, VA 22202-4302, and to the Office of Management and Budget, Paperwork Reduction Project (0704-0188), Washington, DC 20503.

1. AGENCY USE ONLY (Leave blank)		2. REPORT DATE	3. REPORT TYPE AND DATES COVERED FINAL	
4. TITLE AND SUBTITLE SDIO: Discovering Superconducting Materials at High Temperatures			5. FUNDING NUMBERS 61102F 1601/07	
6. AUTHOR(S) Prof Francis J. DiSalvo				
7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES) Cornell University Ithaca, NY 14853			8. PERFORMING ORGANIZATION REPORT NUMBER AFOSR-TR- 95 0124	
9. SPONSORING MONITORING AGENCY NAME(S) AND ADDRESS(ES) AFOSR/NE 110 Duncan Avenue Suite B115 Bolling AFB DC 20332-0001			10. SPONSORING MONITORING AGENCY REPORT NUMBER F49620-93-1-0328	
11. SUPPLEMENTARY NOTES				
12a. DISTRIBUTION AVAILABILITY STATEMENT APPROVED FOR PUBLIC RELEASE: DISTRIBUTION UNLIMITED			12b. DISTRIBUTION CODE	
13. ABSTRACT AND KEYWORDS SEE FINAL REPORT ABSTRACT  <b>19950324 006</b>				
14. SUBJECT TERMS			15. NUMBER OF PAGES	
			16. PRICE CODE	
17. SECURITY CLASSIFICATION OF REPORT UNCLASSIFIED	18. SECURITY CLASSIFICATION OF THIS PAGE UNCLASSIFIED	19. SECURITY CLASSIFICATION OF ABSTRACT UNCLASSIFIED	20. LIMITATION OF ABSTRACT UNCLASSIFIED	



80014

FINAL TECHNICAL REPORT AFOSR-TR- 95 0139

AFOSR, Grant # F49620-93-1-0328

"SDIO: Discovering Superconducting Materials at High Temperatures"

Professor Francis J. DiSalvo  
Department of Chemistry  
Cornell University  
Ithaca, NY 14853

Begin date: June 1, 1993  
Termination Date: May 31, 1994

Report Date: August 25, 1994

Accession For	
NTIS CRA&I	<input checked="" type="checkbox"/>
DTIC TAB	<input type="checkbox"/>
Unannounced	<input type="checkbox"/>
Justification .....	
By .....	
Distribution /	
Availability Codes	
Dist	Avail and/or Special
A-1	

## Final Report

### "Discovering Superconducting Materials at High Temperatures"

Professor Francis J. DiSalvo

The research funded under this grant focused on the layered structure compounds  $\text{BaNiS}_2$  and  $\text{BaCoS}_2$ . The former is a metallic conductor while the latter is a magnetic Mott insulator. We planned doping studies to study the effects of both disorder and the crossover to the metallic state. It is hoped that doping a Mott insulator to the metallic state might produce a high temperature superconductor. Unfortunately, due to the termination of the SDIO program, this research was supported for only one year (instead of the planned three years), so the project is not complete.

We have shown that  $\text{BaNiS}_2$  can be doped by copper to produce  $\text{BaNi}_{1-x}\text{Cu}_x\text{S}_2$  for  $x < 0.5$ . It is rather surprising that this is possible, since in chalcogenides Cu is known to be +1 valence thus it formally requires the Ni to be +3. Of course, considerable covalency will mix the sulfur and nickel orbitals at the Fermi energy and ionic like oxidation states do not obtain. Upon doping with Cu, the metallic  $\text{BaNiS}_2$  becomes less conducting with the room temperature resistance increasing by a factor of three and becoming almost temperature independent. It is likely that the large site disorder on the Ni lattice caused by Cu substitution is pushing the system towards Anderson localization. This work is almost complete and a publication is being readied.

The second phase of this project, doping  $\text{BaCoS}_2$  with K to produce  $\text{Ba}_{1-x}\text{K}_x\text{CoS}_2$ , is only midstream. We are performing K substitution in an attempt to dope this Mott insulator to the metallic state. In fact, while some K doping has occurred, the synthetic methods so far used all lead to some loss of K, which is quite volatile at the reaction temperatures (near 900 C). We are attempting to invent the proper synthetic technology to contain the K, but we are not assured success.

One publication has been accepted as a result of our years work: "Refined Structure and Properties of the Layered Mott Insulator  $\text{BaCoS}_2$ " G. Jeffery Snyder, Maria C. Gelabert and F. J. DiSalvo, to be published in the Journal of Solid State Chemistry.

The graduate students supported in this project have been: Maria Gelabert, Sami Malik and Vincent Balberin.

There have been no patents or disclosures on this project.

